

14. a)	Briefly explain the principle of operation of a Carry-Look ahead Adder (CLA) with the help of a conceptual diagram. How is the ripple effect eliminated? What are its limitations?	4	3	5	2
b)	A CMOS VLSI chip in 1.2V, 100 nm process has 200 million transistors, of which 180 million transistors are in memory arrays. (W/L) ratios of Logic and memory transistors are (6/1) and (2/1) with activities 0.1 and 0.05 respectively. Assuming the transistors have a gate capacitance of 2 fF/ μm , estimate the dynamic power consumption per MHz of the system.	4	4	5	2
15. a)	Compare and contrast a 3T DRAM cell with a standard 6T SRAM cell with suitable schematics.	4	2	6	2
b)	Draw the architecture of a 128K SRAM organized as a 512×256 core array. Estimate the word-line capacitance assuming $C_g = 2\text{fF}$, $C_{sd} = 0.5\text{fF}$ and $C_w = 0.2\text{fF}$.	4	5	6	3
16. a)	Define LE, BE and EE. Find the LE of a NAND4.	4	2	2	2
b)	A simplified clock distribution network is shown below. Assuming the bottom path with 100C is critical, size the inverters using LE technique.	4	4	2	3
17.	Answer any <i>two</i> of the following:				
a)	SRAM DRV.	4	3	6	2
b)	4 bit Barrel Shifter.	4	2	5	1
c)	Standby Power Management in a VLSI Chip.	4	2	5	1

M: Marks; L: Bloom's Taxonomy Level; CO: Course Outcome; PO: Programme Outcome

S. No.	Criteria for questions	Percentage
1	Fundamental knowledge (Level-1 & 2)	50%
2	Knowledge on application and analysis (Level-3 & 4)	37%
3	*Critical thinking and ability to design (Level-5 & 6) (*wherever applicable)	13%